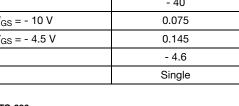


www.vishay.com

Vishay Siliconix

# Automotive P-Channel 40 V (D-S) 175 °C MOSFET

PRODUCT SUMMARY				
V <sub>DS</sub> (V)	- 40			
$R_{DS(on)}(\Omega)$ at $V_{GS}$ = - 10 V	0.075			
$R_{DS(on)}$ ( $\Omega$ ) at $V_{GS}$ = - 4.5 $V$	0.145			
I <sub>D</sub> (A)	- 4.6			
Configuration	Single			

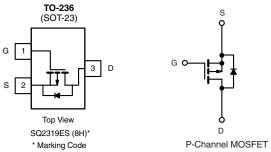


#### **FEATURES**

- Halogen-free According to IEC 61249-2-21 **Definition**
- TrenchFET® Power MOSFET
- AEC-Q101 Qualified<sup>c</sup>
- 100 % Rq and UIS Tested
- Compliant to RoHS Directive 2002/95/EC







ORDERING INFORMATION	
Package	SOT-23
Lead (Pb)-free and Halogen-free	SQ2319ES-T1-GE3

<b>ABSOLUTE MAXIMUM RATING</b>	<b>S</b> ( $T_C = 25  ^{\circ}C$ , unless	ss otherwise noted	d)		
PARAMETER		SYMBOL	LIMIT	UNIT	
Drain-Source Voltage		$V_{DS}$	- 40	V	
Gate-Source Voltage		$V_{GS}$	± 20		
Continuous Drain Current	T <sub>C</sub> = 25 °C	- I <sub>D</sub>	- 4.6		
	T <sub>C</sub> = 125 °C		- 2.6		
Continuous Source Current (Diode Conduction)		I <sub>S</sub>	- 3.7	Α	
Pulsed Drain Current <sup>a</sup>		I <sub>DM</sub>	- 18	1	
Single Pulse Avalanche Current	L = 0.1 mH	I <sub>AS</sub>	- 12		
Single Pulse Avalanche Energy	L = U. I IIIII	E <sub>AS</sub>	7.2	mJ	
Maximum Power Dissipation <sup>a</sup>	T <sub>C</sub> = 25 °C	D	3	10/	
	T <sub>C</sub> = 125 °C	- P <sub>D</sub>	1	W	
Operating Junction and Storage Temperatur	re Range	T <sub>J</sub> , T <sub>stg</sub>	- 55 to + 175	°C	

THERMAL RESISTANCE RATINGS					
PARAMETER		SYMBOL	LIMIT	UNIT	
Junction-to-Ambient	PCB Mount <sup>b</sup>	$R_{thJA}$	166	°C/W	
Junction-to-Foot (Drain)		R <sub>thJF</sub>	50	]	

#### **Notes**

- a. Pulse test; pulse width  $\leq$  300  $\mu$ s, duty cycle  $\leq$  2 %.
- b. When mounted on 1" square PCB (FR-4 material).
- c. Parametric verification ongoing.



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PARAMETER	SYMBOL	TES	TEST CONDITIONS		TYP.	MAX.	UNIT	
Static		-			ı	ı		
Drain-Source Breakdown Voltage	V <sub>DS</sub>	V <sub>GS</sub> = 0, I <sub>D</sub> = - 250 μA		- 40	-	-	V	
Gate-Source Threshold Voltage	V <sub>GS(th)</sub>	V <sub>DS</sub> =	$V_{DS} = V_{GS}, I_D = -250 \mu\text{A}$		- 2.0	- 2.5	V	
Gate-Source Leakage	I <sub>GSS</sub>	$V_{DS} = 0 \text{ V}, V_{GS} = \pm 20 \text{ V}$		-	-	± 100	nA	
Zero Gate Voltage Drain Current		V <sub>GS</sub> = 0 V	V <sub>DS</sub> = - 40 V	-	-	- 1		
	I <sub>DSS</sub>	V <sub>GS</sub> = 0 V	V <sub>DS</sub> = - 40 V, T <sub>J</sub> = 125 °C	-	-	- 50	μΑ	
		V <sub>GS</sub> = 0 V	V <sub>DS</sub> = - 40 V, T <sub>J</sub> = 175 °C	-	-	- 150		
On-State Drain Current <sup>a</sup>	I <sub>D(on)</sub>	V <sub>GS</sub> = - 10 V	$V_{DS} \le -5 V$	- 10	-	-	Α	
Drain-Source On-State Resistance <sup>a</sup>		V <sub>GS</sub> = - 10 V	I <sub>D</sub> = - 3 A	-	0.061	0.075	Ω	
		V <sub>GS</sub> = - 10 V	I <sub>D</sub> = - 3 A, T <sub>J</sub> = 125 °C	-	-	0.116		
	R <sub>DS(on)</sub>	V <sub>GS</sub> = - 10 V	I <sub>D</sub> = - 3 A, T <sub>J</sub> = 175 °C	-	-	0.139		
		V <sub>GS</sub> = - 4.5 V	I <sub>D</sub> = - 2.4 A	-	0.120	0.145		
Forward Transconductanceb	9 <sub>fs</sub>	V <sub>DS</sub> = - 5 V, I <sub>D</sub> = - 3 A		-	8	-	S	
Dynamic <sup>b</sup>		<u> </u>						
Input Capacitance	C <sub>iss</sub>		<sub>S</sub> = 0 V V <sub>DS</sub> = - 25 V, f = 1 MHz	-	493	620	pF	
Output Capacitance	C <sub>oss</sub>	$V_{GS} = 0 V$		-	76	95		
Reverse Transfer Capacitance	C <sub>rss</sub>			-	51	65		
Total Gate Charge <sup>c</sup>	Qg	V <sub>GS</sub> = - 10 V	S = - 10 V V <sub>DS</sub> = - 20 V, I <sub>D</sub> = - 3 A	-	10.5	16	nC	
Gate-Source Charge <sup>c</sup>	Q <sub>gs</sub>			-	1.8	-		
Gate-Drain Charge <sup>c</sup>	Q <sub>gd</sub>			-	2.6	-		
Gate Resistance	R <sub>g</sub>	f = 1 MHz		5	10	15	Ω	
Turn-On Delay Time <sup>c</sup>	t <sub>d(on)</sub>			-	5	8		
Rise Time <sup>c</sup>	t <sub>r</sub>	V <sub>DD</sub> =	$V_{DD} = -20 \text{ V, R}_{1} = 6.7 \Omega$		11	17	ns	
Turn-Off Delay Time <sup>c</sup>	t <sub>d(off)</sub>	$I_D \cong -3 \text{ A}, V_{GEN} = -10 \text{ V}, R_g = 1 \Omega$		-	19	29		
Fall Time <sup>c</sup>	t <sub>f</sub>			-	8	12		
Source-Drain Diode Ratings and Char	acteristics <sup>b</sup>	•						
Pulsed Current <sup>a</sup>	I <sub>SM</sub>			-	-	- 18	Α	
Forward Voltage	V <sub>SD</sub>	I <sub>F</sub> = - 1.5 A, V <sub>GS</sub> = 0		_	- 0.8	- 1.2	V	

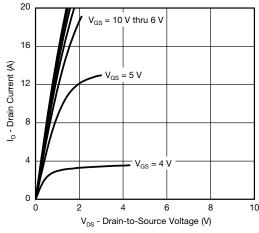
#### Notes

- a. Pulse test; pulse width  $\leq 300~\mu s,~duty~cycle \leq 2~\%.$
- b. Guaranteed by design, not subject to production testing.
- c. Independent of operating temperature.

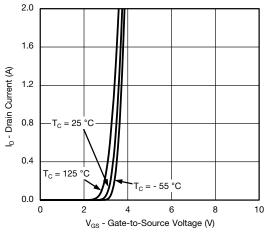
Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.



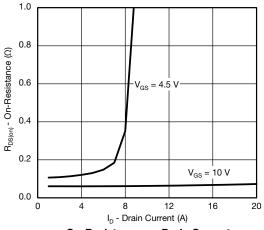
#### **TYPICAL CHARACTERISTICS** (T<sub>A</sub> = 25 °C, unless otherwise noted)



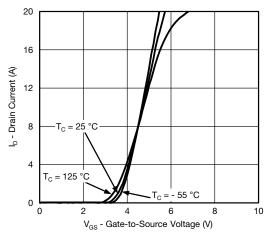




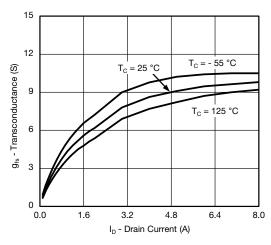
**Transfer Characteristics** 



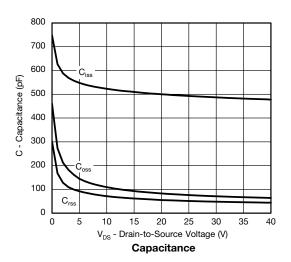
**On-Resistance vs. Drain Current** 



**Transfer Characteristics** 

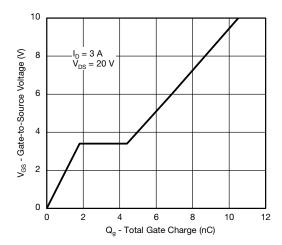


Transconductance

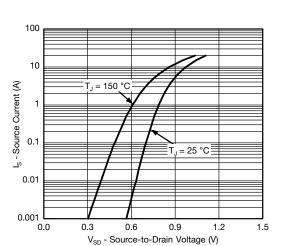




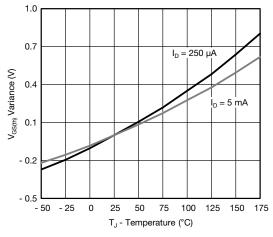
### TYPICAL CHARACTERISTICS (T<sub>A</sub> = 25 °C, unless otherwise noted)



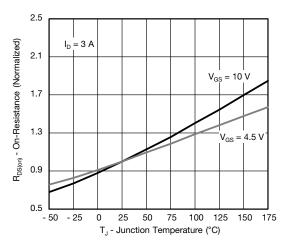
**Gate Charge** 



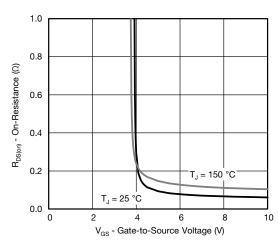
Source Drain Diode Forward Voltage



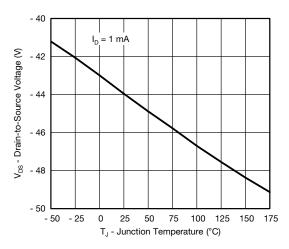
Threshold Voltage



On-Resistance vs. Junction Temperature



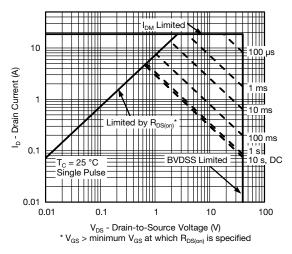
On-Resistance vs. Gate-to-Source Voltage



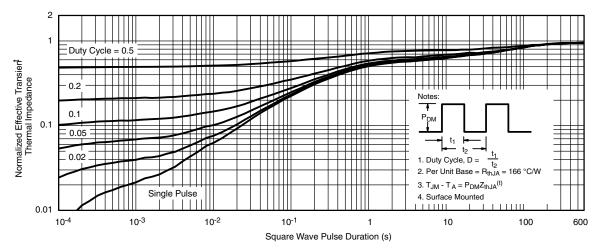
**Drain Source Breakdown vs. Junction Temperature** 



### **THERMAL RATINGS** ( $T_A = 25$ °C, unless otherwise noted)



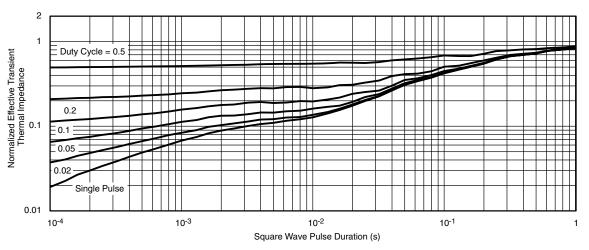
#### Safe Operating Area



Normalized Thermal Transient Impedance, Junction-to-Ambient



### **THERMAL RATINGS** (T<sub>A</sub> = 25 °C, unless otherwise noted)



Normalized Thermal Transient Impedance, Junction-to-Foot

#### Note

- The characteristics shown in the two graphs
- Normalized Transient Thermal Impedance Junction-to-Ambient (25 °C)
- Normalized Transient Thermal Impedance Junction-to-Foot (25 °C)

are given for general guidelines only to enable the user to get a "ball park" indication of part capabilities. The data are extracted from single pulse transient thermal impedance characteristics which are developed from empirical measurements. The latter is valid for the part mounted on printed circuit board - FR4, size 1" x 1" x 0.062", double sided with 2 oz. copper, 100 % on both sides. The part capabilities can widely vary depending on actual application parameters and operating conditions.

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